

AMENDMENTSIN THE CLAIMS

1-241. (canceled)

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242. (previously presented) A chip packaging method comprising:

joining a die and a substrate;

after said joining said die and said substrate, depositing a passive device over
said substrate, wherein said passive device has a portion not over said die; and

10 separating said substrate.

243. (currently amended) A chip packaging method comprising:

joining a die and a substrate;

after said joining said die and said substrate, depositing a passive device

15 having over said substrate, wherein said passive device has a first connection point[[end]] connected [[down]] to said die and a second end connected to a topmost pad of
said chip package; [[and]]after said depositing said passive device, depositing a metal bump connected to
a second connection point of said passive device; and

20 separating said substrate.

244. (currently amended) A chip packaging method comprising:

providing a first die having a first top surface at a horizontal level;providing a second die having a second top surface at said horizontal level;25 depositing a passive device over said horizontal level, wherein said passive
device has a portion not over said first and second dies; die; anddepositing a metal trace over said horizontal level, wherein said metal trace has a
portion not over said first and second dies, die.

30 245. (new) The method of claim 242, wherein said substrate comprises metal.

246. (new) The method of claim 242 further comprising joining a film and said substrate followed by said joining said die and said substrate, an opening in said film exposing said substrate.

5 247. (new) The method of claim 246, wherein forming said opening in said film comprising punching.

248. (new) The method of claim 246, wherein said film comprises metal.

10 249. (new) The method of claim 242, after said joining said die and said substrate, further comprising depositing a patterned circuit layer over said die and over said substrate, followed by said separating said substrate, wherein said patterned circuit layer extends to a place not over said die.

15 250. (new) The method of claim 249, wherein said depositing said patterned circuit layer comprises electroplating.

251. (new) The method of claim 249, wherein said depositing said patterned circuit layer comprises sputtering.

20 252. (new) The method of claim 242, wherein said depositing said passive device comprises electroplating.

253. (new) The method of claim 242, wherein said depositing said passive device comprises sputtering.

254. (new) The method of claim 242, after said joining said die and said substrate, further comprising depositing a solder bump over said substrate, followed by said separating said substrate.

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255. (new) The method of claim 242, after said joining said die and said substrate, further comprising depositing a gold bump over said substrate, followed by said separating said substrate.

5 256. (new) The method of claim 242, wherein said depositing said passive device is followed by said separating said substrate.

257. (new) The method of claim 243, wherein said substrate comprises metal.

10 258. (new) The method of claim 243 further comprising joining a film and said substrate followed by said joining said die and said substrate, an opening in said film exposing said substrate.

15 259. (new) The method of claim 258, wherein forming said opening in said film comprising punching.

260. (new) The method of claim 258, wherein said film comprises metal.

261. (new) The method of claim 243, after said joining said die and said substrate, further comprising depositing a patterned circuit layer over said die and over said substrate, followed by said separating said substrate, wherein said patterned circuit layer extends to a place not over said die.

262. (new) The method of claim 261, wherein said depositing said patterned circuit layer comprises electroplating.

263. (new) The method of claim 261, wherein said depositing said patterned circuit layer comprises sputtering.

30 264. (new) The method of claim 243, wherein said depositing said passive device comprises electroplating.

265. (new) The method of claim 243, wherein said depositing said passive device comprises sputtering.

266. (new) The method of claim 243, wherein said depositing said metal bump 5 comprises depositing a solder bump connected to said second connection point.

267. (new) The method of claim 243, wherein said depositing said metal bump comprises depositing a gold bump connected to said second connection point.

10 268. (new) The method of claim 243, wherein said depositing said metal bump is followed by said separating said substrate.

269. (new) The method of claim 244, wherein said depositing said metal trace comprises electroplating.

15 270. (new) The method of claim 244, wherein said depositing said metal trace comprises sputtering.

271. (new) The method of claim 244, wherein said depositing said passive device 20 comprises electroplating.

272. (new) The method of claim 244, wherein said depositing said passive device comprises sputtering.

25 273. (new) The method of claim 244, after said depositing said passive device and said depositing said metal trace, further comprising depositing a solder bump over said horizontal level.

30 274. (new) The method of claim 244, after said depositing said passive device and said depositing said metal trace, further comprising depositing a gold bump over said horizontal level.